

isc N-Channel MOSFET Transistor

IPD088N06N3G

• FEATURES

- With TO-252(DPAK) packaging
- With low gate drive requirements
- Very high commutation ruggedness
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• APPLICATIONS

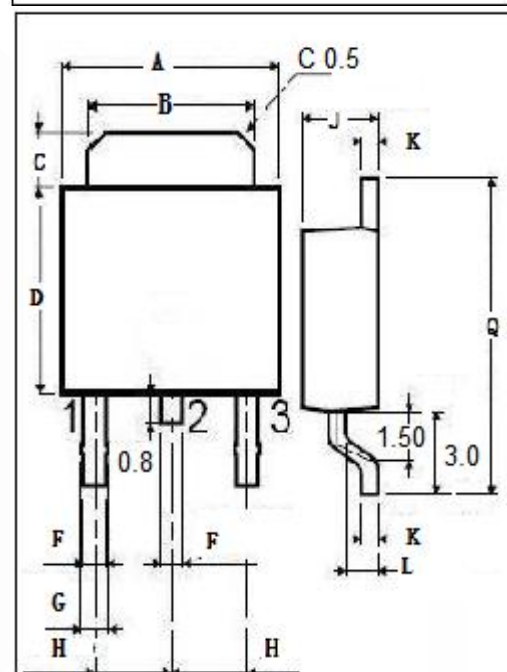
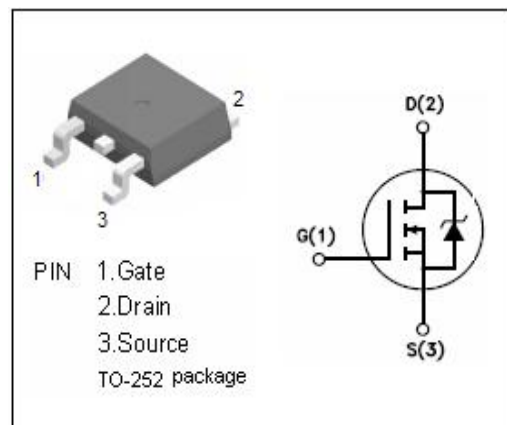
- Switching applications
- LCD&PDP TV
- PC silverbox
- UPS and solar

• ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-Continuous@ $T_c=25^{\circ}\text{C}$ $T_c=100^{\circ}\text{C}$	50 47	A
I_{DM}	Drain Current-Single Pulsed	200	A
P_D	Total Dissipation	71	W
T_j	Operating Junction Temperature	-55~175	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~175	$^{\circ}\text{C}$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(ch-c)}$	Channel-to-case thermal resistance	2.1	$^{\circ}\text{C/W}$
$R_{th(ch-a)}$	Channel-to-ambient thermal resistance	62	$^{\circ}\text{C/W}$



DIM	mm	
	MIN	MAX
A	6.40	6.60
B	5.20	5.40
C	1.15	1.35
D	5.70	6.10
F	0.65	
G	0.75	
H	2.10	2.50
J	2.10	2.40
K	0.40	0.60
L	0.90	1.10
Q	9.90	10.1

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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V; I_D=1mA$	60			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=\pm 20V; I_D=0.034mA$	2		4	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10V; I_D=50A$		7.1	8.8	$m\Omega$
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V; V_{DS}=0V$			± 0.1	μA
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=60V; V_{GS}=0V@T_j=25^{\circ}\text{C}$ $T_j=125^{\circ}\text{C}$			1 100	μA
V_{SDF}	Diode forward voltage	$I_{SD}=50A, V_{GS}=0V$			1.2	V